CJD31C NPN
CJD32C PNP

COMPLEMENTARY SILICON POWER TRANSISTOR

DPAK TRANSISTOR CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD31C, CJD32C types are Complementary Silicon Power Transistors manufactured by the epitaxial base process, mounted in a surface mount package designed for power amplifier and high speed switching applications.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: (T_C=25°C unless otherwise noted)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	3.0	A
Peak Collector Current	I_{CM}	5.0	A
Base Current	I_B	1.0	A
Power Dissipation	P_D	15	W
Power Dissipation (T_A=25°C)	P_D	1.56	W
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JC}	8.33	°C/W
Thermal Resistance	Θ_{JA}	80.1	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEO}	V_{CE}=60V		50	μA
I_{CES}	V_{CE}=100V		20	μA
I_{EBO}	V_{EB}=5.0V		1.0	mA
BV_{CEO}	I_C=30mA	100		V
$V_{CE(SAT)}$	I_C=3.0A, I_B=375mA		1.2	V
$V_{BE(ON)}$	V_{CE}=4.0V, I_C=3.0A		1.8	V
h_{FE}	V_{CE}=4.0V, I_C=1.0A	25		
h_{FE}	V_{CE}=4.0V, I_C=3.0A	10	50	
f_T	V_{CE}=10V, I_C=500mA, f=1.0MHz	3.0		MHz
h_{fe}	V_{CE}=10V, I_C=500mA, f=1.0kHz	20		

R1 (26-September 2002)

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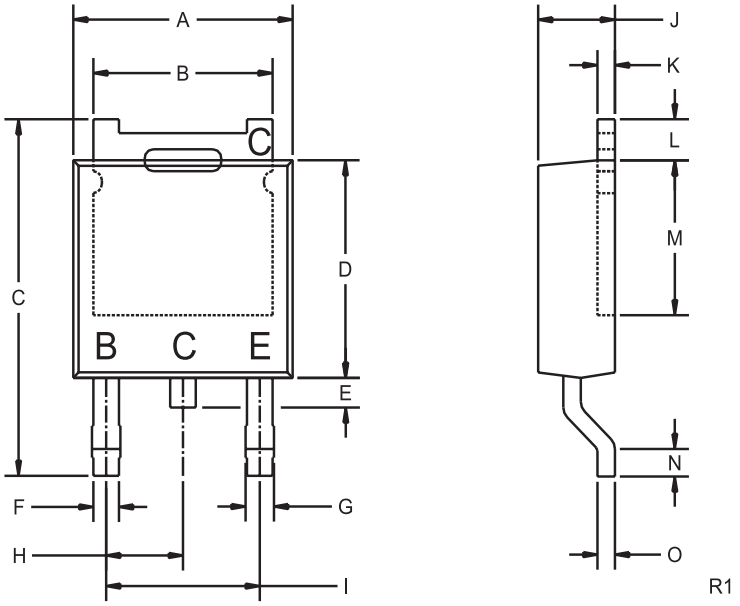
DPAK TRANSISTOR CASE - MECHANICAL OUTLINE



LEAD CODE:
B) BASE
C) COLLECTOR
E) EMITTER
C) COLLECTOR

MARKING CODE:
FULL PART
NUMBER

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.250	0.265	6.35	6.73
B	0.205	0.215	5.21	5.46
C	0.374	0.409	9.50	10.40
D	0.235	0.245	5.97	6.22
E	0.025	0.040	0.64	1.02
F	0.025	0.035	0.64	0.88
G	0.030	0.045	0.76	1.14
H	0.090		2.28	
I	0.180		4.57	
J	0.086	0.094	2.19	2.38
K	0.018	0.023	0.46	0.58
L	0.040	0.050	1.02	1.27
M	0.170	-	4.32	-
N	0.020	-	0.51	-
O	0.018	0.023	0.46	0.58

DPAK TRANSISTOR (REV: R1)

R1 (26-September 2002)